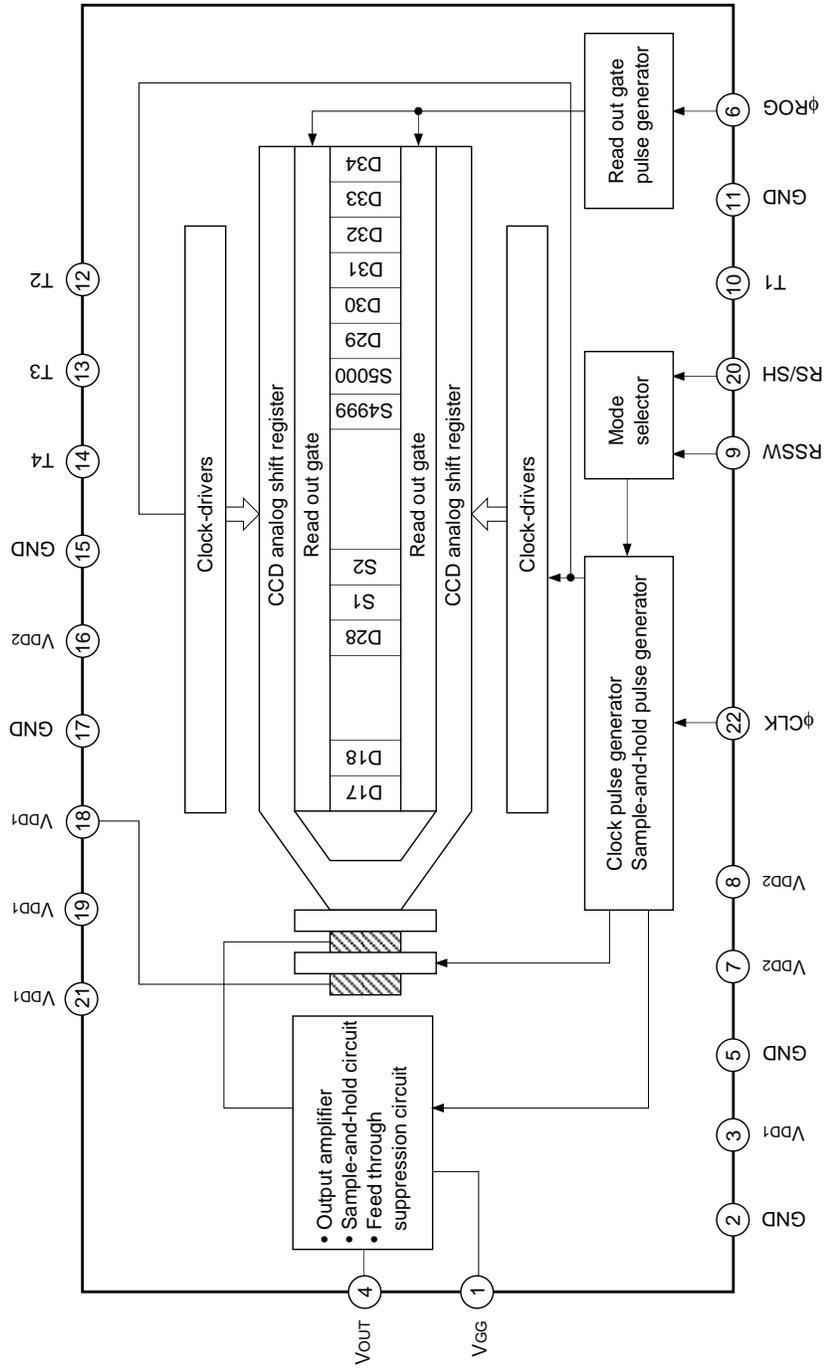


Block Diagram



Pin Description

Pin No.	Symbol	Description
1	V _{GG}	Output circuit gate bias
2	GND	GND
3	V _{DD1}	9V power supply
4	V _{OUT}	Signal output
5	GND	GND
6	φ _{ROG}	Clock pulse
7	V _{DD2}	5V power supply
8	V _{DD2}	5V power supply
9	RSSW*1	Reset pulse switchover pin
10	T1	Test pin (5V)
11	GND	GND
12	T2	Test pin (GND)
13	T3	Test pin (5V)
14	T4	Test pin (GND)
15	GND	GND
16	V _{DD2}	5V power supply
17	GND	GND
18	V _{DD1}	9V power supply
19	V _{DD1}	9V power supply
20	RS/SH*1	Clock pulse or with S/H; without S/H switch
21	V _{DD1}	9V power supply
22	φ _{CLK}	Clock pulse

*1 Output mode is changeable as follows.

20pin 9pin	GND	V _{DD1}	φ _{RS}
GND	Internal RS without S/H	Internal RS with S/H	—
V _{DD1}	—	—	External RS without S/H

Recommended Voltage

Item	Min.	Typ.	Max.	Unit
V _{DD1}	8.5	9.0	9.5	V
V _{DD2}	4.75	5.0	5.25	V

Note) Rules for raising and lowering power supply voltage

To raise power supply voltage, first raise V_{DD1} (9V) and then V_{DD2} (5V).

To lower voltage, first lower V_{DD2} (5V) and then V_{DD1} (9V).

Clock Characteristics

Item	Symbol	Min.	Typ.	Max.	Unit
Input capacity of ϕ CLK pin	C ϕ CLK	—	10	—	pF
Input capacity of ϕ ROG pin	C ϕ ROG	—	10	—	pF
Input capacity of RS/SH pin	C _{RS/SH}	—	10	—	pF
Frequency of ϕ CLK	f ϕ CLK	—	1	12.5	MHz
Frequency of ϕ RS	f ϕ RS	—	1	12.5	MHz

Electro-optical Characteristics (Note 1)

(Ta = 25°C, V_{DD1} = 9V, V_{DD2} = 5V, φCLK = 1MHz, Internal φRS mode without S/H,
Light source = 3200K, IR cut filter, CM-500S (t = 1.0mm))

Item	Symbol	Min.	Typ.	Max.	Unit	Remarks
Sensitivity 1	R1	7.5	10.8	13.9	V/(lx · s)	Note 2
Sensitivity 2	R2	—	24.6	—	V/(lx · s)	Note 3
Sensitivity nonuniformity	PRNU	—	4	10	%	Note 4
Saturation output voltage	V _{SAT}	1.0	1.5	—	V	Note 5
Saturation exposure	SE	0.072	0.139	—	lx · s	Note 6
Even and odd black level DC difference	ΔV	—	1.0	10.0	mV	Note 7
Dark voltage average	V _{DRK}	—	0.3	2	mV	Note 8
Dark signal nonuniformity	DSNU	—	0.6	3	mV	Note 9
Image lag	IL	—	0.02	—	%	Note 10
9V supply current	I _{VDD1}	—	16	32	mA	—
5V supply current	I _{VDD2}	—	3	7	mA	—
Total transfer efficiency	TTE	92	98	—	%	—
Output impedance	Z _O	—	600	—	Ω	—
Offset level	V _{OS}	—	3.0	—	V	Note 11
Dynamic range	DR	500	5000	—	—	Note 12

Notes)

- 1) In accordance with the given electrooptical characteristics, the even black level is defined as the mean value of D8, D10, D12 to D14.
The odd black level is defined as the mean value of D7, D9, D11 and D13.
- 2) For the sensitivity test light is applied with a uniform intensity of illumination.
- 3) W lamp (2854K)
- 4) PRNU is defined as indicated below. Ray incidence conditions are the same as for Note 2.

$$\text{PRNU} = \frac{(V_{\text{MAX}} - V_{\text{MIN}})/2}{V_{\text{AVE}}} \times 100 [\%]$$

Where the 5000 pixels are divided into blocks of 100, even and odd pixels, respectively. The maximum output of each block is set to V_{MAX}, the minimum output to V_{MIN} and the average output to V_{AVE}.

- 5) Use below the minimum value of the saturation output voltage.
- 6) Saturation exposure is defined as follows.

$$\text{SE} = \frac{V_{\text{SAT}}}{R1}$$

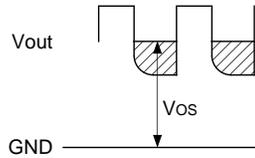
- 7) Indicates the DC difference in value between odd black level and even black level.
- 8) Optical signal accumulated time τ int stands at 10ms.

- 9) The difference between the maximum and mean values of the dark output voltage is calculated for even and odd respectively. The larger value is defined as the dark signal nonuniformity.

Optical signal accumulated time τ_{int} stands at 10ms.

- 10) $V_{OUT} = 500mV$ (Typ.)

- 11) V_{os} is defined as indicated below.

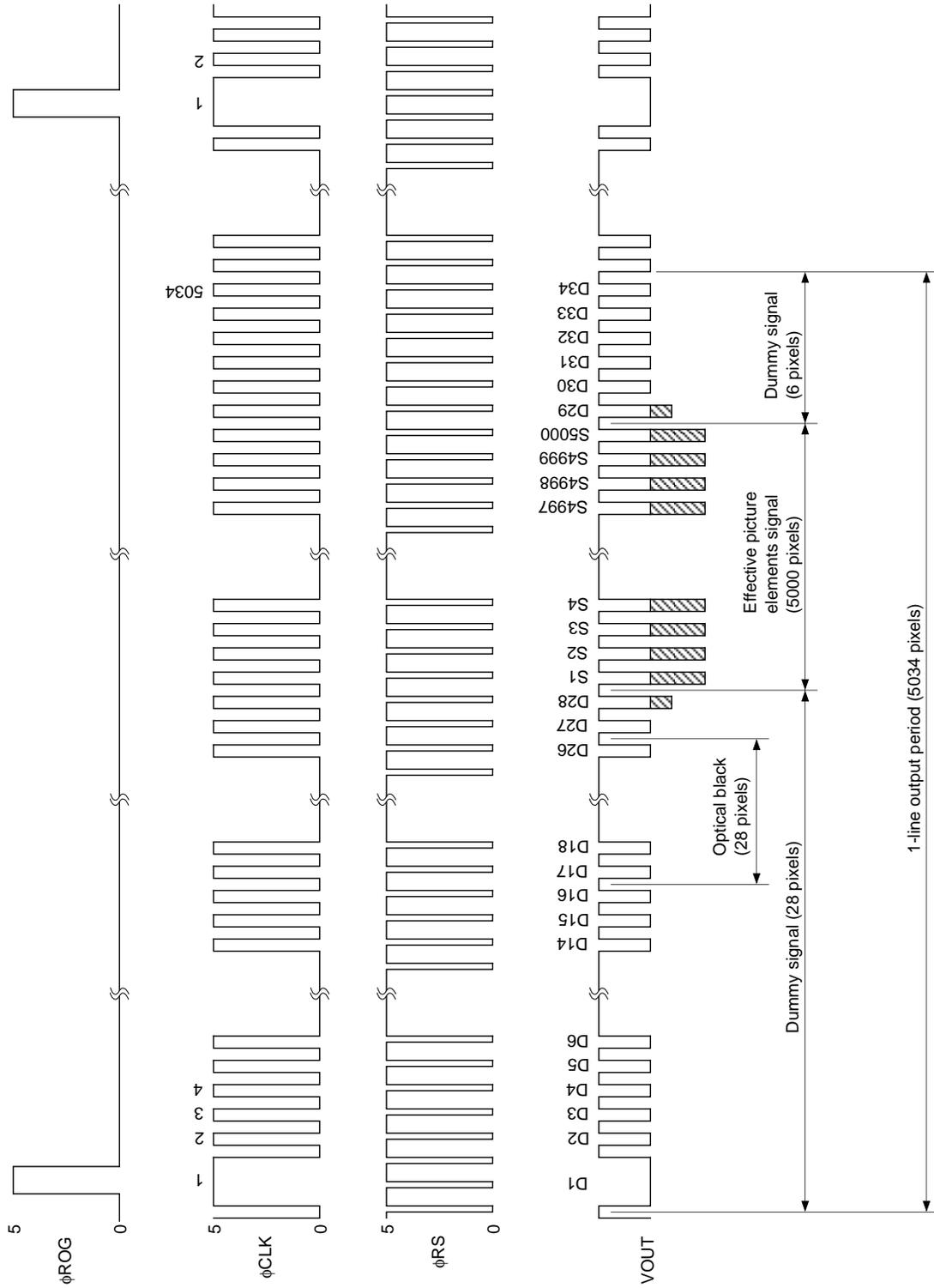


- 12) Dynamic range is defined as follows.

$$DR = \frac{V_{SAT}}{V_{DRK}}$$

When optical accumulated time is shorter, the dynamic range gets wider because dark voltage is in proportion to optical accumulated time.

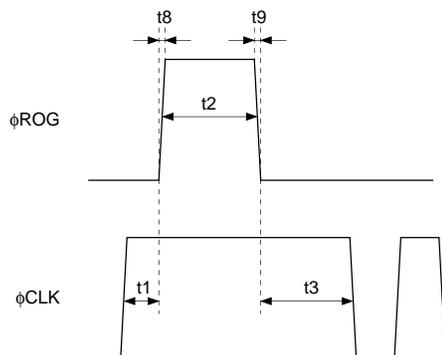
Clock Timing Diagram*



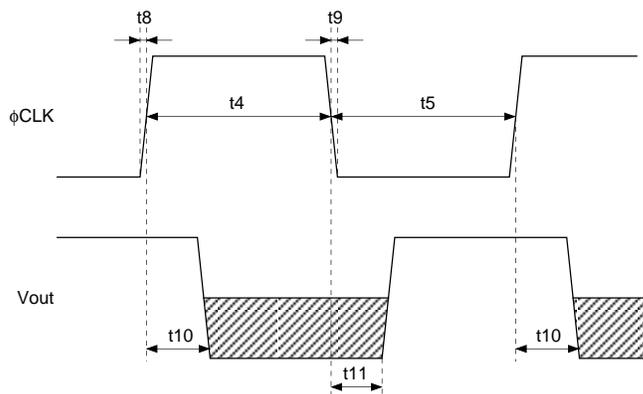
* This clock timing diagram shows when ϕ RS is used externally.

Clock Pulse Waveform Conditions

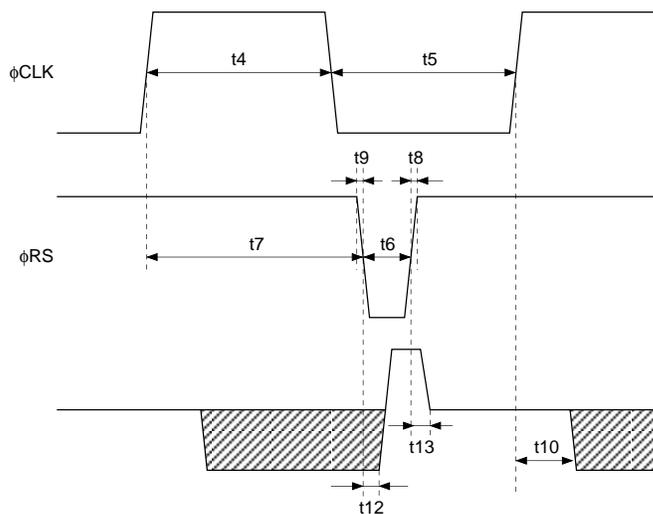
ϕ CLK, ϕ ROG pulse related



Internal ϕ RS mode



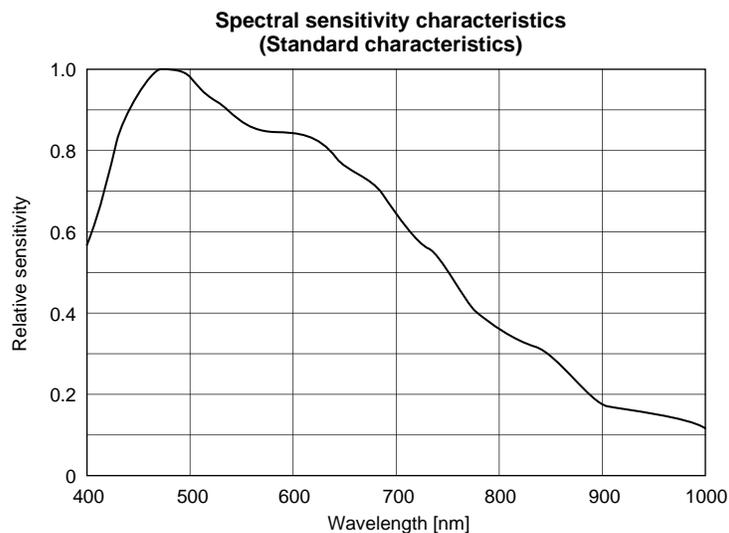
External ϕ RS mode



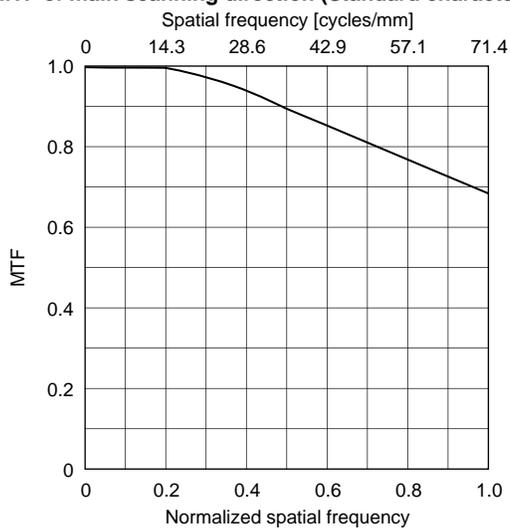
Item	Symbol	Min.	Typ.	Max.	Unit	
ϕ ROG, ϕ CLK pulse timing	t1	100	200	—	ns	
ϕ ROG, ϕ CLK pulse timing	t3	800	1000	—	ns	
ϕ ROG pulse high level period	t2	800	1000	—	ns	
ϕ CLK pulse high level period	t4	40	500*1	—	ns	
ϕ CLK pulse low level period	t5	40	500*1	—	ns	
ϕ RS pulse low level period	t6	25	100*1	—	ns	
ϕ CLK, ϕ RS pulse timing	t7	60	550*1	10 + t4 + t5	ns	
Input clock pulse rise/fall time	t8, t9	—	5	10	ns	
Input clock pulse voltage	High level	$V_{\phi\text{CLK}}, V_{\phi\text{ROG}}$	4.5	5.0	5.5	V
	Low level	$V_{\phi\text{RS}}$	0	—	0.5	V
Signal output delay time	Internal ϕ RS	t10	—	95	—	ns
		t11	—	70	—	ns
	External ϕ RS	t12	—	45	—	ns
		t13	—	60	—	ns

*1 Recommended condition during ϕ CLK = 1MHz.

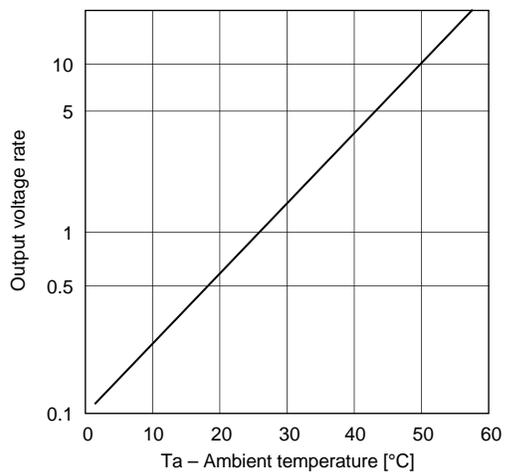
Example of Representative Characteristics ($V_{DD1} = 9V$, $V_{DD2} = 5V$, $T_a = 25^\circ C$)



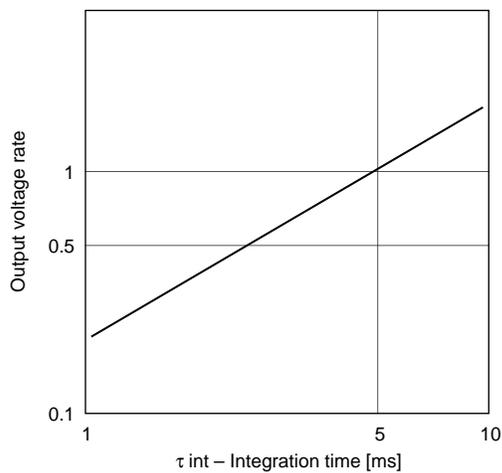
MTF of main scanning direction (Standard characteristics)



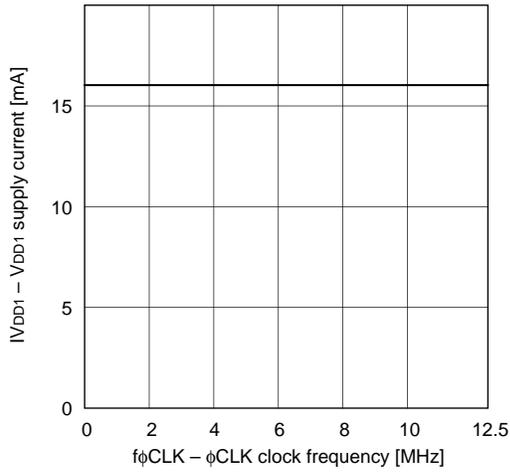
**Dark signal output temperature characteristics
(Standard characteristics)**



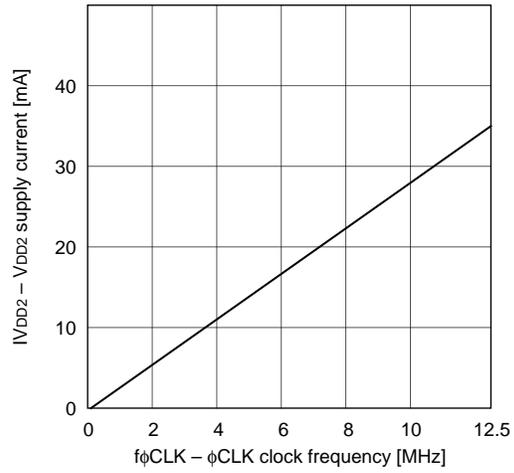
**Integration time output voltage characteristics
(Standard characteristics)**



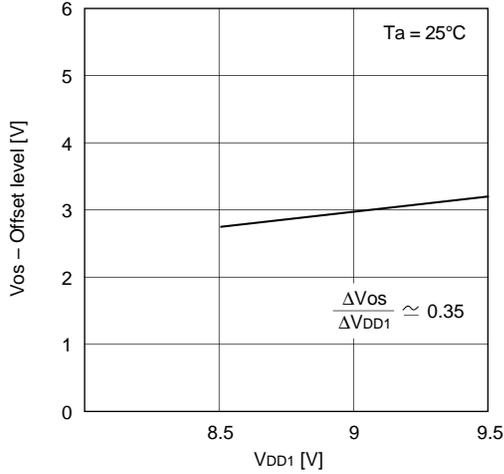
Operational frequency characteristics of the VDD1 supply current (Standard characteristics)



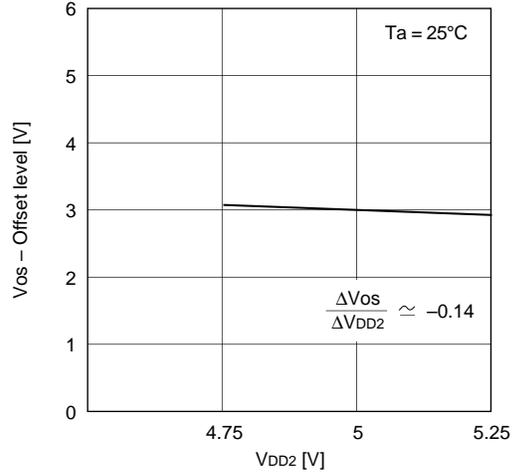
Operational frequency characteristics of the VDD2 supply current (Standard characteristics)



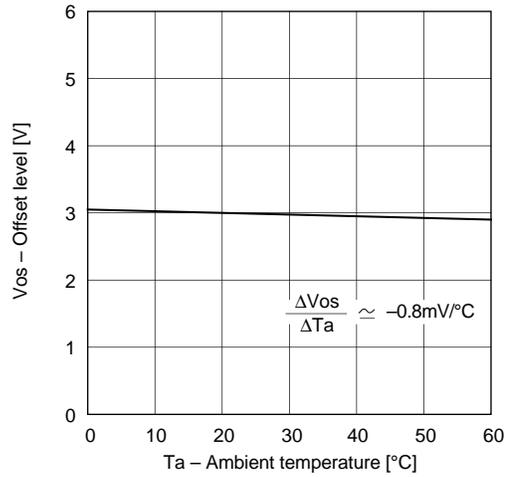
Offset level vs. VDD1 characteristics (Standard characteristics)



Offset level vs. VDD2 characteristics (Standard characteristics)



Offset level vs. Temperature characteristics (Standard characteristics)



Notes on Handling

- 1) Static charge prevention
CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.
 - a) Either handle bare handed or use non chargeable gloves, clothes or material. Also use conductive shoes.
 - b) When handling directly use an earth band.
 - c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
 - d) Ionized air is recommended for discharge when handling CCD image sensor.
 - e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

- 2) Regulation for raising and lowering the power supply voltage
When raising the supply voltage, first raise V_{DD1} (9V) and then V_{DD2} (5V).
Similarly, lower V_{DD2} (5V) first and then V_{DD1} (9V).

- 3) Soldering
 - a) Make sure the package temperature does not exceed 80°C.
 - b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a grounded 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
 - c) To dismount an image sensor, do not use a solder suction equipment.
When using an electric desoldering tool, ground the controller. For the control system, use a zero cross type.

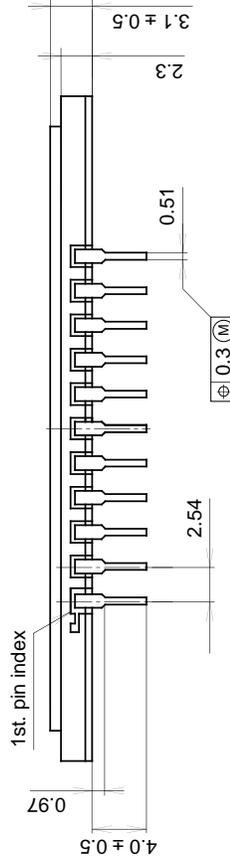
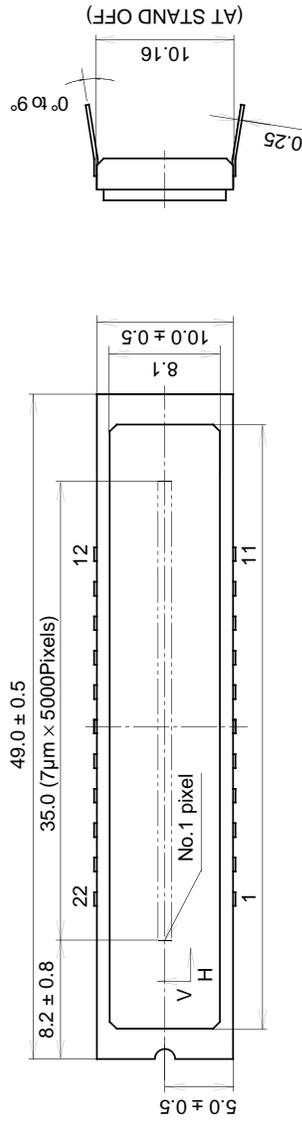
- 4) Dust and dirt protection
 - a) Operate in clean environments.
 - b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
 - c) Clean with a cotton bud and ethyl alcohol if the grease stained.
Be careful not to scratch the glass.
 - d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.

- 5) Exposure to high temperatures or humidity will affect the characteristics.
Accordingly avoid storage or usage in such conditions.

- 6) CCD image sensors are precise optical equipment that should not be subject to mechanical shocks.

Package Outline Unit: mm

22pin DIP (400mil)



1. The height from the bottom to the sensor surface is 1.42 ± 0.3 mm.
2. The thickness of the cover glass is 0.8mm, and the refractive index is 1.5.

PACKAGE STRUCTURE

PACKAGE MATERIAL	Ceramic
LEAD TREATMENT	TIN PLATING
LEAD MATERIAL	42 ALLOY
PACKAGE WEIGHT	3.9g